

ETC

Notice of Allowability	Application No.		Applicant(s)	
	10/789,209		FREDERIC GAILLARD	
	Examiner		Art Unit	
	David Nhu		2818	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to 3/28/05.
2. ☒ The allowed claim(s) is/are 1-20.
3. ☒ The drawings filed on 27 February 2004 are accepted by the Examiner.
4. ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). 09/021,788; 09/553,461
09/465,233; 09/162,915
09/679,843; 09/185,555
09/247,381
 a) ☐ All b) ☐ Some* c) ☐ None of the:
 1. ☐ Certified copies of the priority documents have been received.
 2. ☒ Certified copies of the priority documents have been received in Application No. 10/632,179.
 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

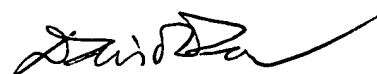
* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
6. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 1) ☐ hereto or 2) ☐ to Paper No./Mail Date _____.
 (b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.
 Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
7. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- | | |
|--|---|
| 1. <input type="checkbox"/> Notice of References Cited (PTO-892) | 5. <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 2. <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 6. <input type="checkbox"/> Interview Summary (PTO-413),
Paper No./Mail Date _____ |
| 3. <input checked="" type="checkbox"/> Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date <u>01</u> | 7. <input type="checkbox"/> Examiner's Amendment/Comment |
| 4. <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit
of Biological Material | 8. <input checked="" type="checkbox"/> Examiner's Statement of Reasons for Allowance |
| | 9. <input type="checkbox"/> Other _____ |



REASONS FOR ALLOWANCE

2. Claims 1-20 are allowed.

3. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests in claims 1, 10, 16: A method for processing a substrate, comprising: reacting an organosilicon compound with carbon dioxide and one or more oxidizing gases selected from the group consisting of oxygen, ozone, nitrous oxide, carbon monoxide, and water to deposit a dielectric layer comprising silicon, carbon, and oxygen on the substrate; and depositing a layer of comprising silicon and carbon on the dielectric layer (as cited in claim 1); reacting an alkylsilane having one methyl group bonded to silicon with carbon dioxide and one or more oxidizing gases selected from the group consisting of oxygen, ozone, nitrous oxide, carbon monoxide, and water to deposit a dielectric layer comprising silicon, carbon, and oxygen on the substrate; and depositing a layer of comprising silicon and carbon on the dielectric layer (as cited in claim 10); introducing an oxidizing gas comprising carbon dioxide and one or more oxidizing gases selected from the group consisting of oxygen, ozone, nitrous oxide, carbon monoxide, and water into the chamber; depositing the dielectric layer using a CVD process at a substrate temperature between about 170 °C and about 180 °C, wherein the dielectric layer comprises silicon, oxygen, and carbon; and depositing a layer comprising silicon and carbon on the dielectric layer (as cited in claim 16).

4. Applicants filed an amendment on 3/24/05, and also filed at that time a **terminal disclaimer statement with reference to U.S. Patent No. 6,627,532 B1.**

5. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the

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issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

CONCLUSION

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Gaillard et al (6,627,532 B1): Method of Decreasing the K Value in SiOC Layer Deposited by CVD.

7. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu, (703) 306- 5796. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (703) 308-4910.

The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7382.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

David Nhu



April 30, 2005



DAVID NHU
PRIMARY EXAMINER